

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP40T17A uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

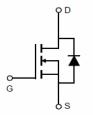
- V_{DS} =40V, I_D =170A $R_{DS(ON)}$ =1.4mΩ (typical) @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Schematic Diagram



Marking and pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40T17A	NCEP40T17A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	170	Α
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	120	Α
Pulsed Drain Current	I _{DM}	680	Α
Maximum Power Dissipation	P _D	250	W
Derating factor		1.66	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1200	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

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NCEP40T17A

Thermal Characteristic

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =85A	-	1.4	1.7	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =85A	-	80	-	S
Dynamic Characteristics (Note4)	<u> </u>					
Input Capacitance	C _{lss}	\/ -20\/\/ -0\/	-	5670	-	PF
Output Capacitance	Coss	V_{DS} =20V, V_{GS} =0V, F=1.0MHz	-	1930	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	62	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	13.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =20 V , I_{D} =85 A	-	7.2	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	55	-	nS
Turn-Off Fall Time	t _f		-	8.6	-	nS
Total Gate Charge	Qg)/ 00\/ L 05A	-	88.6	-	nC
Gate-Source Charge	Q_{gs}	$V_{DS}=20V, I_{D}=85A,$	-	16		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	13		nC
Drain-Source Diode Characteristics	<u> </u>					
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =85A	-		1.2	٧
Diode Forward Current (Note 2)	Is		-	-	170	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = I_S$	-		33	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-		119	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=20V,VG=10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics

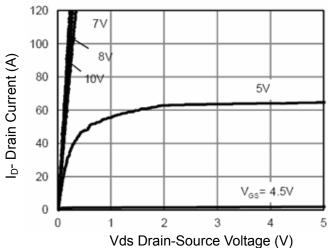


Figure 1 Output Characteristics

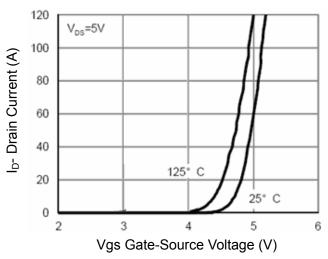


Figure 2 Transfer Characteristics

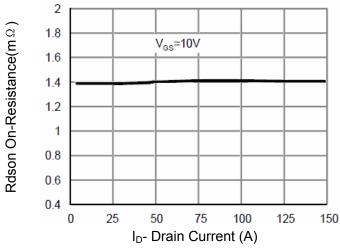


Figure 3 Rdson- Drain Current

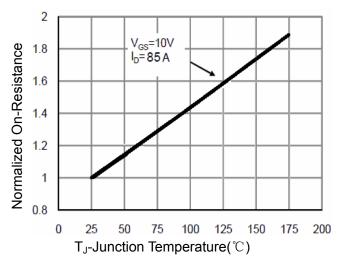


Figure 4 Rdson-Junction Temperature

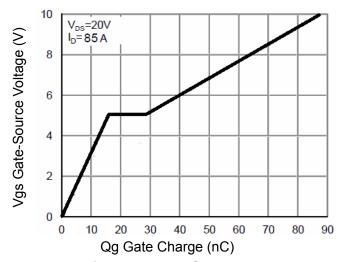


Figure 5 Gate Charge

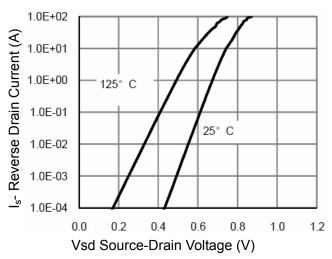


Figure 6 Source- Drain Diode Forward



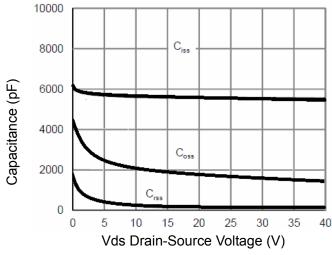


Figure 7 Capacitance vs Vds

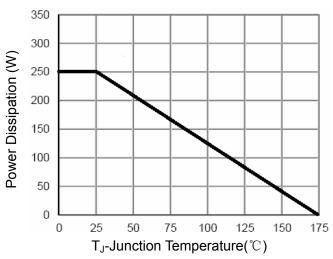


Figure 9 Power De-rating

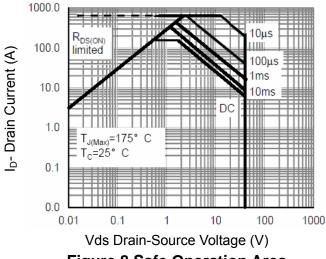


Figure 8 Safe Operation Area

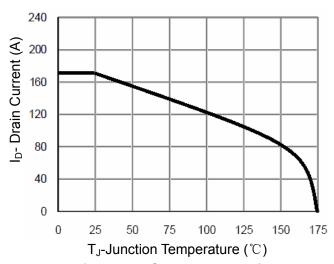


Figure 10 Current De-rating

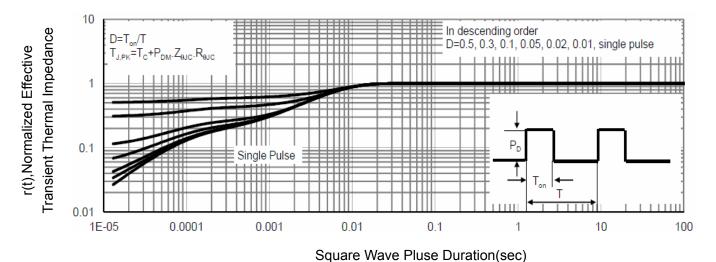
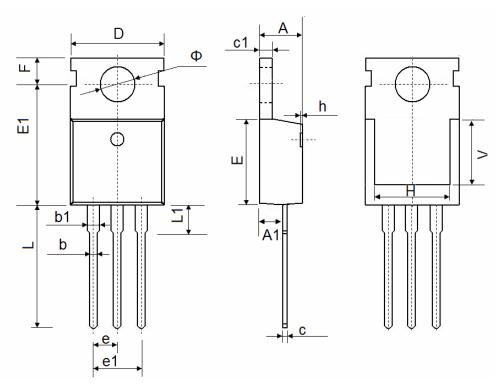


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



O-mak-d	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
А	4.400	4.600	0.173	0.181		
A1	2.250	2.550	0.089	0.100		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.330	0.650	0.013	0.026		
c1	1.200	1.400	0.047	0.055		
D	9.910	10.250	0.390	0.404		
E	8.9500	9.750	0.352	0.384		
E1	12.650	12.950	0.498	0.510		
е	2.54	TYP.	0.100 TYP.			
e1	4.980	5.180	0.196	0.204		
F	2.650	2.950	0.104	0.116		
Н	7.900	8.100	0.311	0.319		
h	0.000	0.300	0.000	0.012		
L	12.900	13.400	0.508	0.528		
L1	2.850	3.250	0.112	0.128		
V	7.500	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150		



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